

(54) MANUFACTURE OF ACTIVE MATRIX DISPLAY DEVICE

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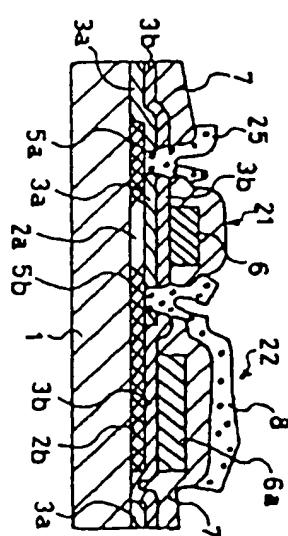
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PURPOSE: To provide an active matrix display device equipped with both a TFT having a gate insulating film of high withstand voltage and an additional capacity of a large capacity value.

CONSTITUTION: That part of a first insulating film 3a which is placed on a first capacity electrode 2b is removed and a second insulating film 3b is formed over the whole surface of a substrate 1, the first insulating film 3a being formed over the whole surface of the substrate 1. A gate insulating film comprises two layers of films, i.e., a first insulating film 3a and second insulating film 3b. An additional-capacity insulating film for an additional capacity comprising a first capacity electrode 2b and second capacity electrode 6a comprises only the second insulating film 3b. Because the thickness of the layer of the gate insulating film can be set independently of that of the layer of the additional-capacity insulating film, the thickness of each layer can be set properly.



(54) LIGHT RECEIVER

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